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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK1836, 2SK1837

Silicon N-Channel MOS FET

RENESAS

ADE-208-1326 (Z)
1st. Edition
Mar. 2001

Application

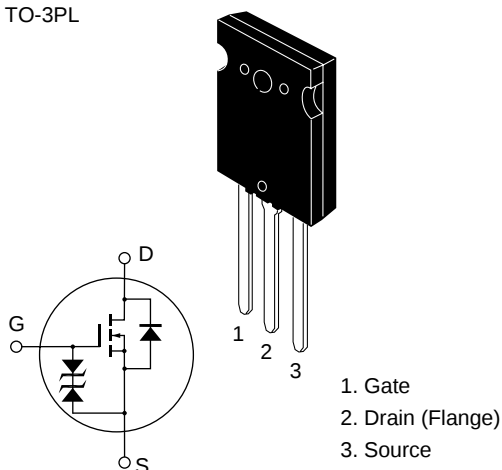
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

Outline

TO-3PL



Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	K1836	V_{DSS}	450	V
	K1837		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	50	A
Drain peak current		$I_{D(pulse)}^{*1}$	200	A
Body to drain diode reverse drain current		I_{DR}	50	A
Channel dissipation		P_{ch}^{*2}	250	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55 to +150	°C

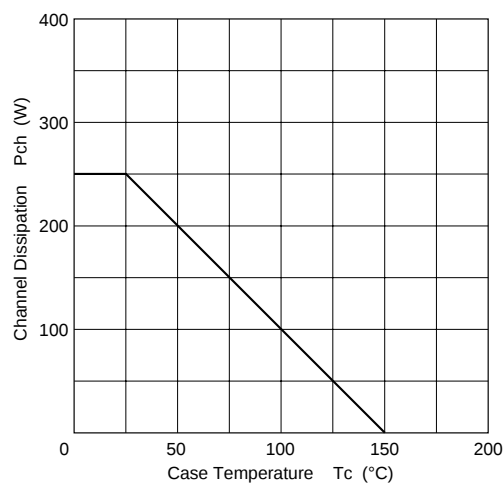
Notes 1. PW 10 μs, duty cycle 1 %
2. Value at Tc = 25 °C

Electrical Characteristics (Ta = 25°C)

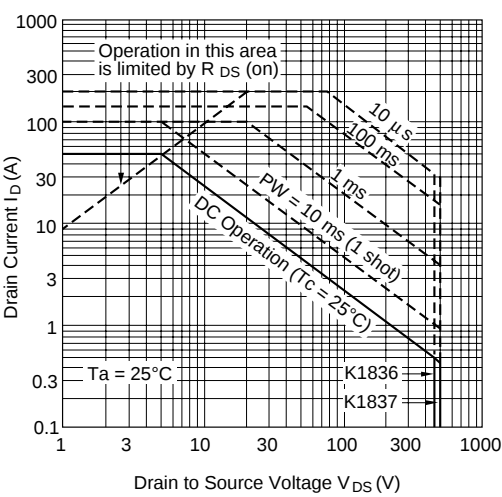
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	K1836	$V_{(BR)DSS}$	450	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
	K1837		500	—	—		
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	K1836	I_{DSS}	—	—	250	μA	$V_{DS} = 360 \text{ V}$, $V_{GS} = 0$
	K1837						$V_{DS} = 400 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	K1836	$R_{DS(on)}$	—	0.08	0.10		$I_D = 25 \text{ A}$
	K1837		—	0.085	0.11		$V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance		$ y_{fs} $	22	35	—	S	$I_D = 25 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		C_{iss}	—	8150	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance		C_{oss}	—	2100	—	pF	$V_{GS} = 0$
Reverse transfer capacitance		C_{rss}	—	180	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time		$t_{d(on)}$	—	80	—	ns	$I_D = 25 \text{ A}$
Rise time		t_r	—	250	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time		$t_{d(off)}$	—	550	—	ns	$R_L = 1.2$
Fall time		t_f	—	220	—	ns	
Body to drain diode forward voltage		V_{DF}	—	1.1	—	V	$I_F = 50 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time		t_{rr}	—	620	—	ns	$I_F = 50 \text{ A}$, $V_{GS} = 0$, $di_F / dt = 100 \text{ A} / \mu\text{s}$

Note 1. Pulse Test

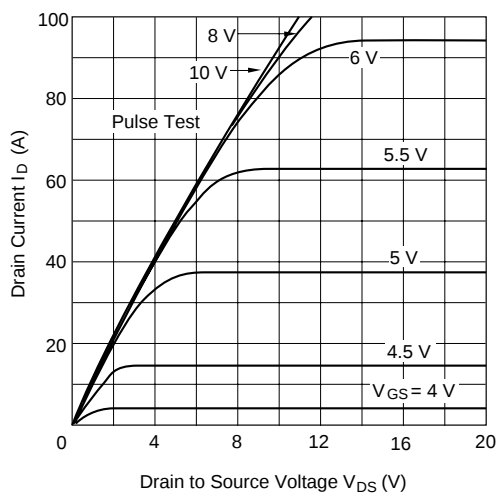
Power vs. Temperature



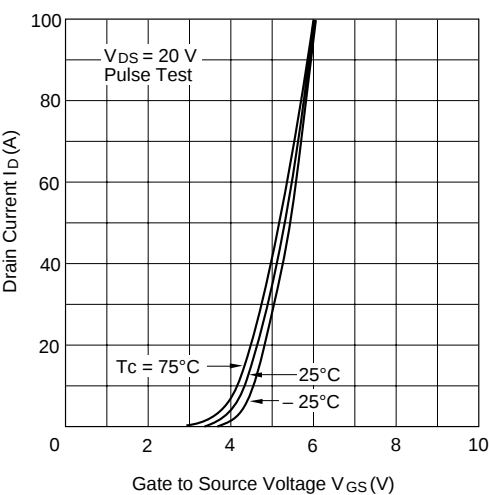
Maximum Safe Operation Area



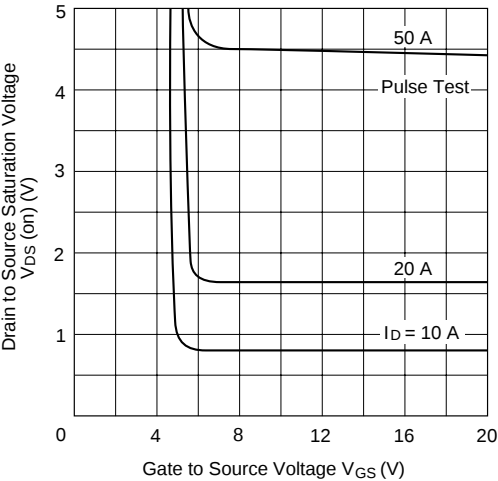
Typical Output Characteristics



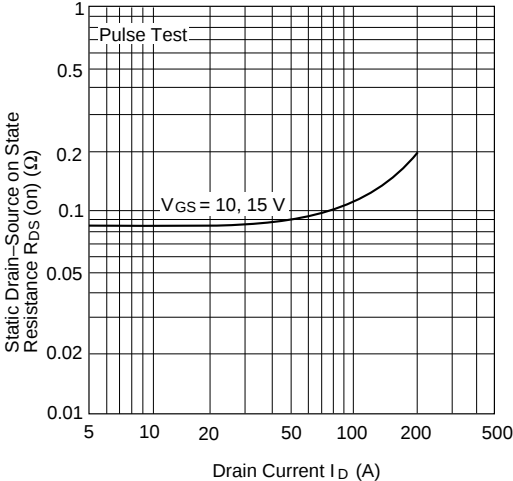
Typical Transfer Characteristics



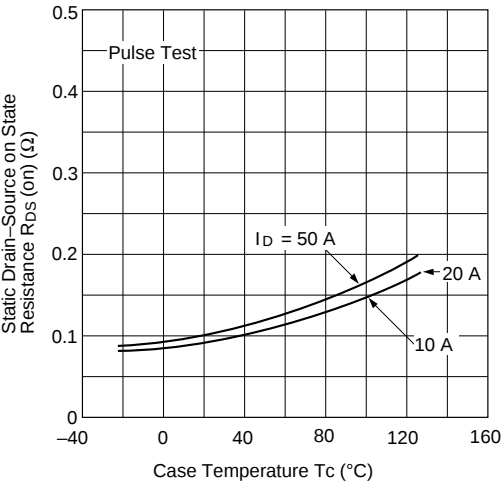
Drain to Source Saturation Voltage
vs. Gate to Source Voltage



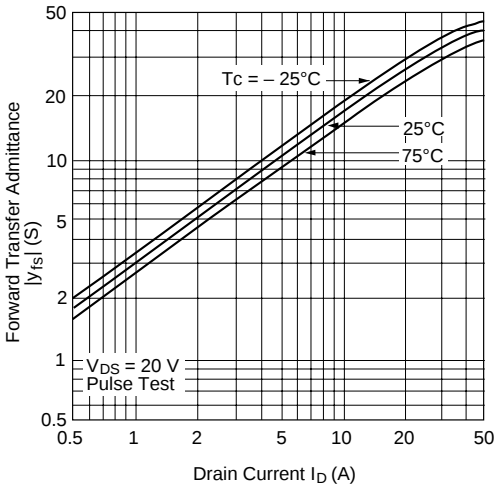
Static Drain to Source on State
Resistance vs. Drain Current



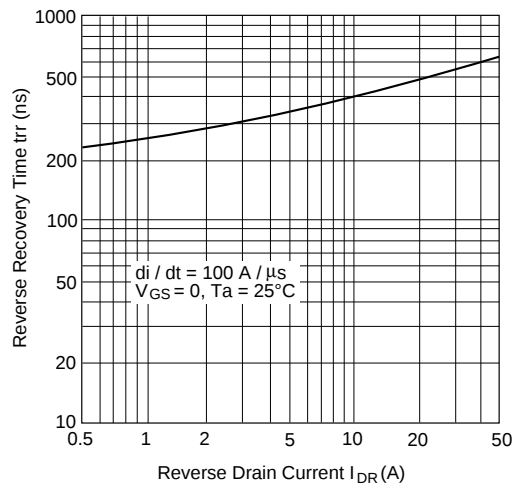
Static Drain to Source on State
Resistance vs. Temperature



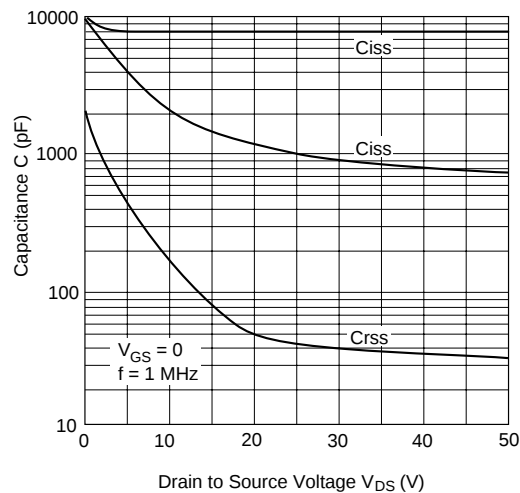
Forward Transfer Admittance
vs. Drain Current



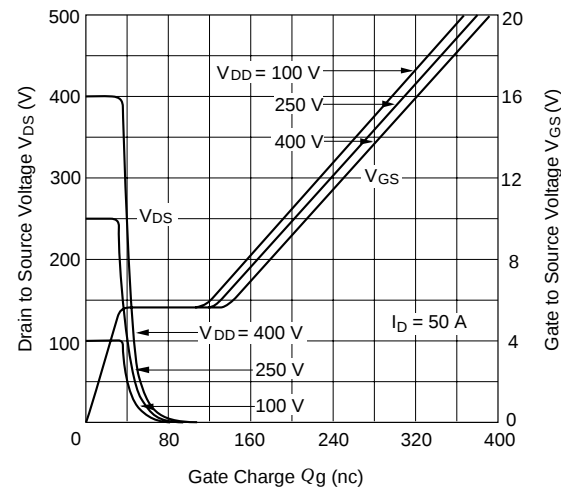
Body to Drain Diode Reverse
Recovery Time



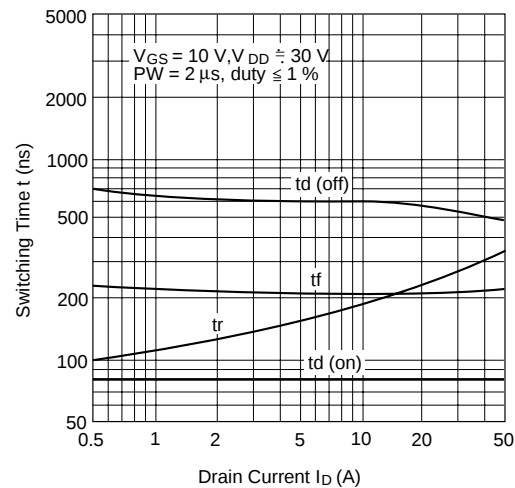
Typical Capacitance
vs. Drain to Source Voltage

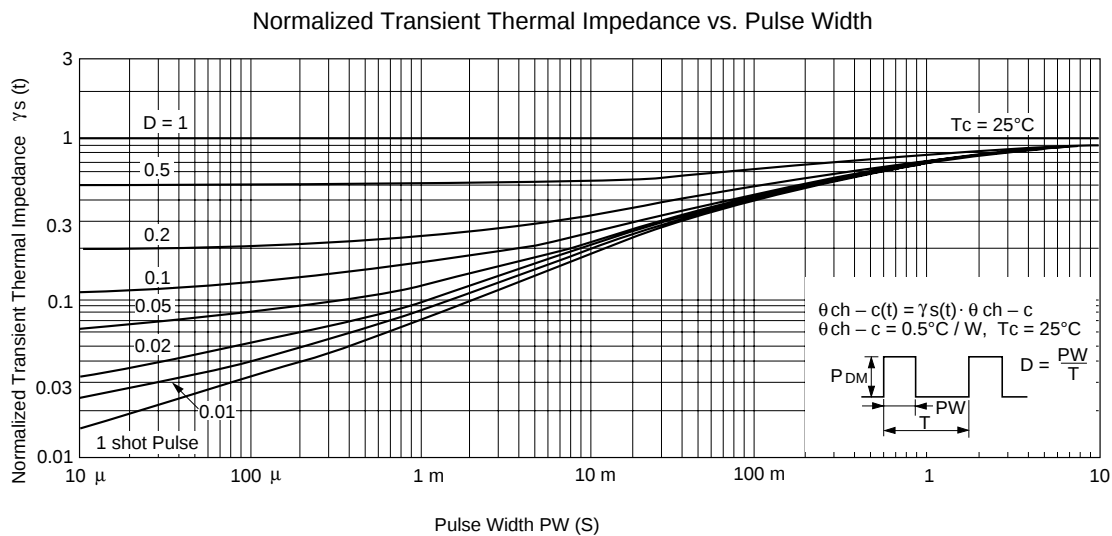
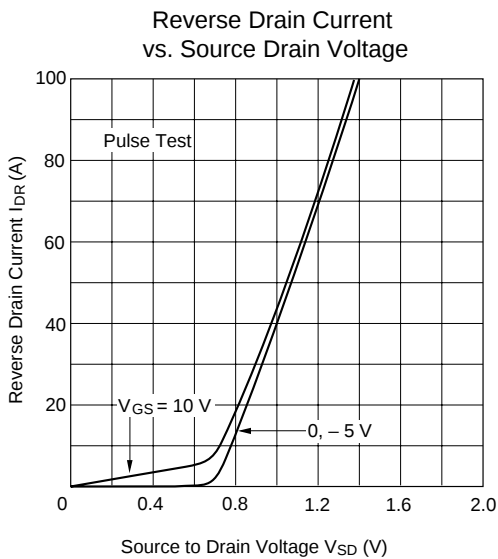


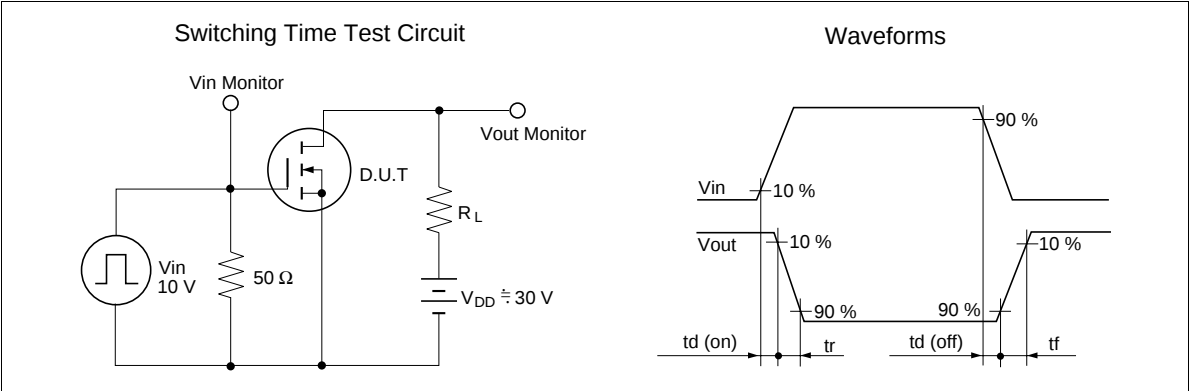
Dynamic Input Characteristics



Switching Characteristics

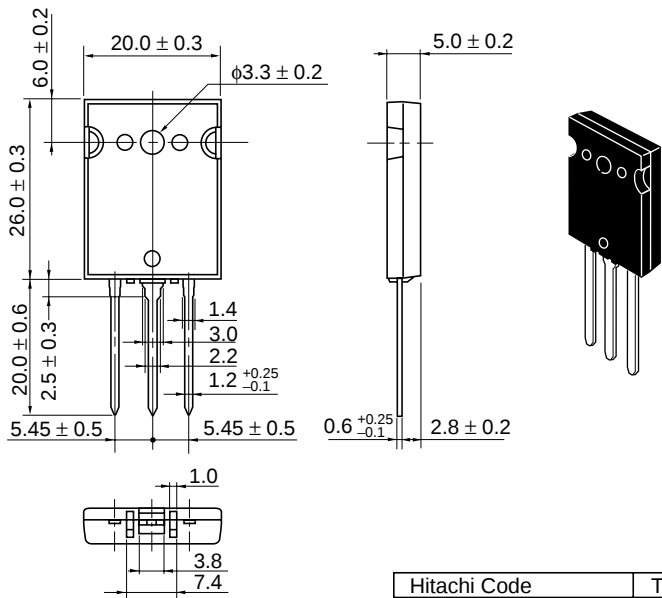






Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-3PL
JEDEC	—
EIAJ	—
Mass (reference value)	9.9 g

Cautions

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